

## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device including: a semiconductor substrate of a first conductivity type; a cladding layer of the first conductivity type provided on the semiconductor substrate; an active layer provided on the cladding layer of the first conductivity type, the active layer having a super-lattice structure including a disordered region in a vicinity of at least one cavity end face; a first cladding layer of a second conductivity type provided on the active layer; an etching stop layer of the second conductivity type provided on the first cladding layer; and a second cladding layer of the second conductivity type provided on the etching stop layer, the second cladding layer forming a ridge structure, the ridge structure extending along a cavity length direction and having a predetermined width. A concentration of an impurity in the etching stop layer in the vicinity of the at least one cavity end face is greater than a concentration of the impurity in the interior of a cavity and equal to or smaller than about  $2 \times 10^{18} \text{ cm}^{-3}$ .